

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A manufacturing method of an SOI wafer, comprising:
~~bonding a wafer for active layer with a supporting wafer via an insulating film interposed therebetween to thereby form a bonded wafer; and then~~
~~reducing a film thickness in a part of said active layer wafer of said bonded wafer to thereby form an SOI layer for manufacturing said SOI wafer; preparing a supporting wafer contains comprising boron by in an amount of 9×10^{18} atoms/cm³ or more; and~~
~~forming a rear surface insulating film on a one surface opposite to the bonding surface of the said supporting wafer prior to said bonding; ;~~
~~ion-implanting hydrogen gas or a noble gas element to an active layer wafer to thereby form an ion-implanted layer in said active layer wafer;~~
~~bonding said active layer wafer with a the other surface of said supporting wafer via an insulating film interposed therebetween to thereby form a bonded wafer; and then~~
~~heat treating said bonded wafer to thereby induce cleavage in a portion of said bonded wafer at the site of the ion-implanted layer as an interface to thereby form an SOI layer with said remaining active layer wafer for manufacturing said SOI wafer.~~

2. (Cancelled)

3. (Currently Amended) A manufacturing method of an SOI wafer in accordance with claim 1, ~~in which~~ wherein a thickness of the SOI layer is less than 0.10 μm .

4, 9 - 21. (Cancelled)